

### FRED Ultrafast Soft Recovery Diode 60A / 1200V

#### FEATURES

- Ultrafast recovery
- 150 °C operating junction temperature
- Designed and qualified for industrial level
- Planar FRED Chip

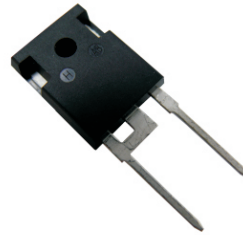
#### BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

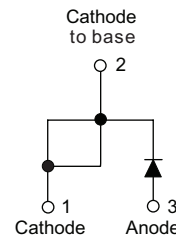
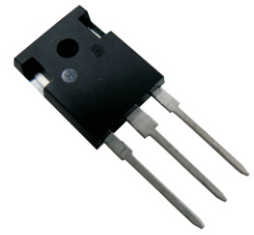
#### DESCRIPTION/APPLICATIONS

- Anti-parallel diode for switching mode power supply and inverters.
- Free wheeling diode for motor controllers and inverters.
- Snubber diode
- Uninterruptible power supply (UPS)
- HF welder
- Induction heating
- High speed rectifiers

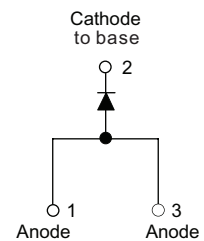
60EPU12



60APU12



TO-247AC modified



TO-247AB

#### PRODUCT SUMMARY

$t_{rr}$	45 ns
$I_{F(AV)}$	60 A
$V_R$	1200 V

#### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	$V_R$		1200	V
Continuous forward current	$I_{F(AV)}$	$T_C = 60\text{ °C}$	60	A
Single pulse forward current	$I_{FSM}$	$T_C = 25\text{ °C}$	570	
Maximum repetitive forward current	$I_{FRM}$	Square wave, 20 kHz	100	
Operating junction and storage temperatures	$T_j, T_{Stg}$		- 55 to 150	°C

#### ELECTRICAL SPECIFICATIONS ( $T_J = 25\text{ °C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_R$	$I_R = 100\mu A$	1200	-	-	V
Forward voltage	$V_F$	$I_F = 60A$	-	2.1	2.3	
		$I_F = 120A$	-	-	3.0	
		$I_F = 60A, T_J = 125\text{ °C}$	-	-	2.0	
Reverse leakage current	$I_R$	$V_R = V_R$ rated	-	1.0	10	$\mu A$
		$T_J = 150\text{ °C}, V_R = V_R$ rated	-	-	500	
Junction capacitance	$C_T$	$V_R = 200V$	-	37	-	pF
Series inductance	$L_S$	Measure lead to lead 5mm from package body	-	10	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 0.5A, I <sub>R</sub> = 1A, I <sub>RR</sub> = 0.25A (RG#1 CKT)	-	65	70	ns
		I <sub>F</sub> = 1A, dI <sub>F</sub> /dt = 200 A/μs, V <sub>R</sub> = 30V	-	45	-	
		T <sub>J</sub> = 25°C	-	330	-	
		T <sub>J</sub> = 125°C	-	430	-	
Peak recovery current	I <sub>RRM</sub>	I <sub>F</sub> = 60 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 800 V	T <sub>J</sub> = 25°C	-	5	A
			T <sub>J</sub> = 125°C	-	12	
Reverse recovery charge	Q <sub>rr</sub>		T <sub>J</sub> = 25°C	-	650	nC
			T <sub>J</sub> = 125°C	-	2800	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R <sub>thJC</sub>		-	65	0.40	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>		-	45	40	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	5.5	-	g
			-	0.2	-	oz.
Mounting torque			0.6 (5)	-	1.2 (10)	N · m (lbf · in)
Marking device		Case style TO-247AC modified	60EPU12			
		Case style TO-247AC	60APU12			

Fig.1 Maximum effective transient thermal impedance, junction-to-case vs. pulse duration

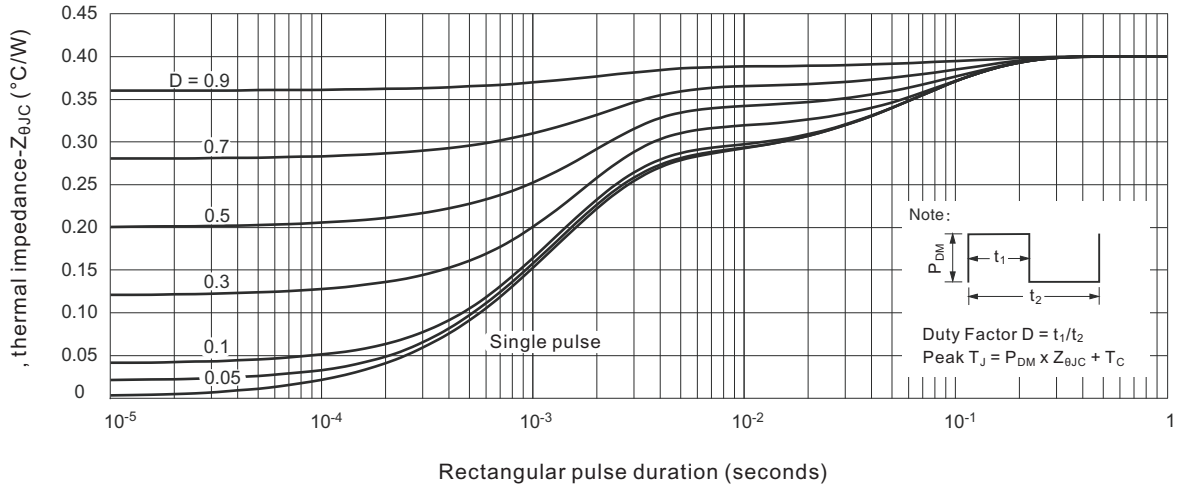


Fig.2 Forward current vs. forward voltage

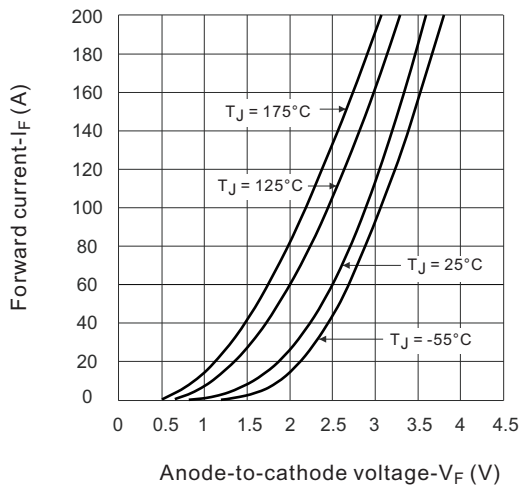


Fig.3. Reverse recovery time vs. current rate of change

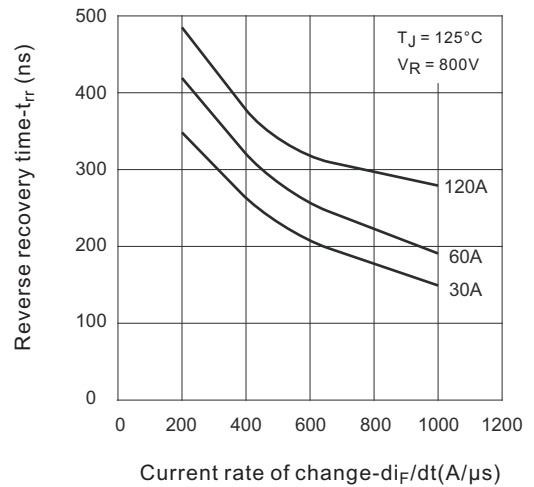


Fig.4 Reverse recovery charge vs. current rate of change

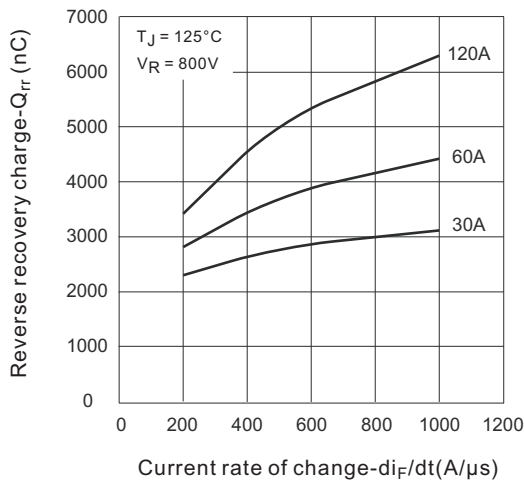
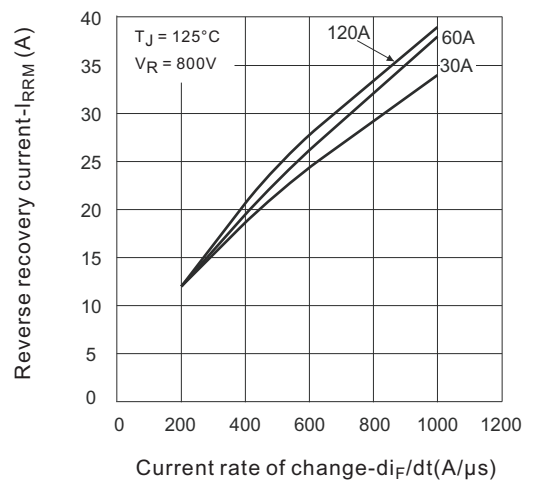


Fig.5 Reverse recovery current vs. current rate of change



## Nell High Power Products

Fig.6 Dynamic parameters vs. junction temperature

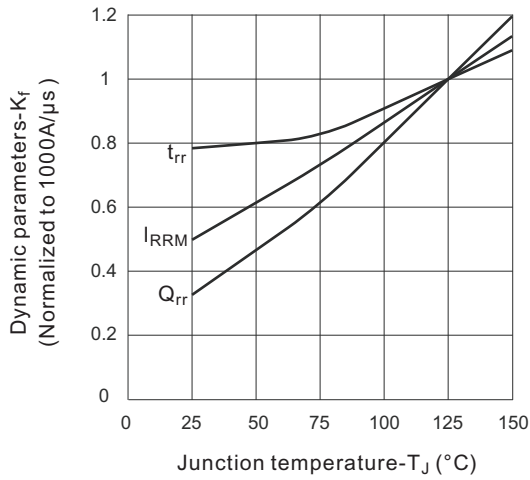


Fig.7 Maximum average forward current vs. case temperature

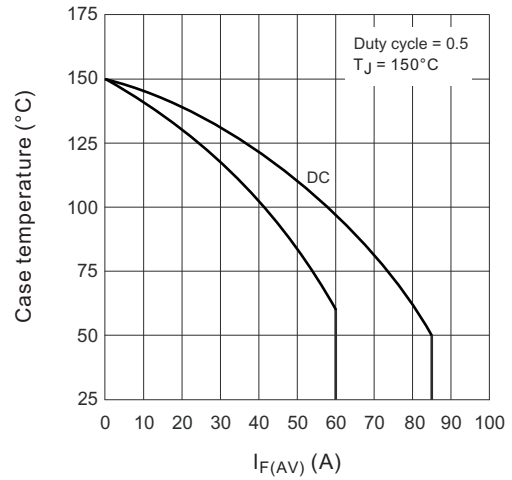
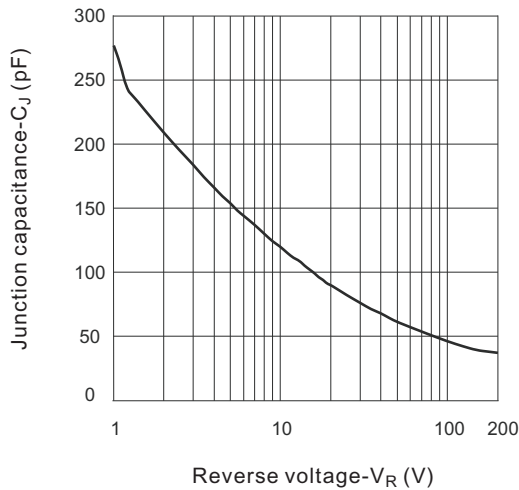
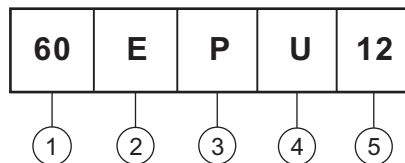


Fig.8 Junction capacitance vs. reverse voltage



### Ordering Information Table

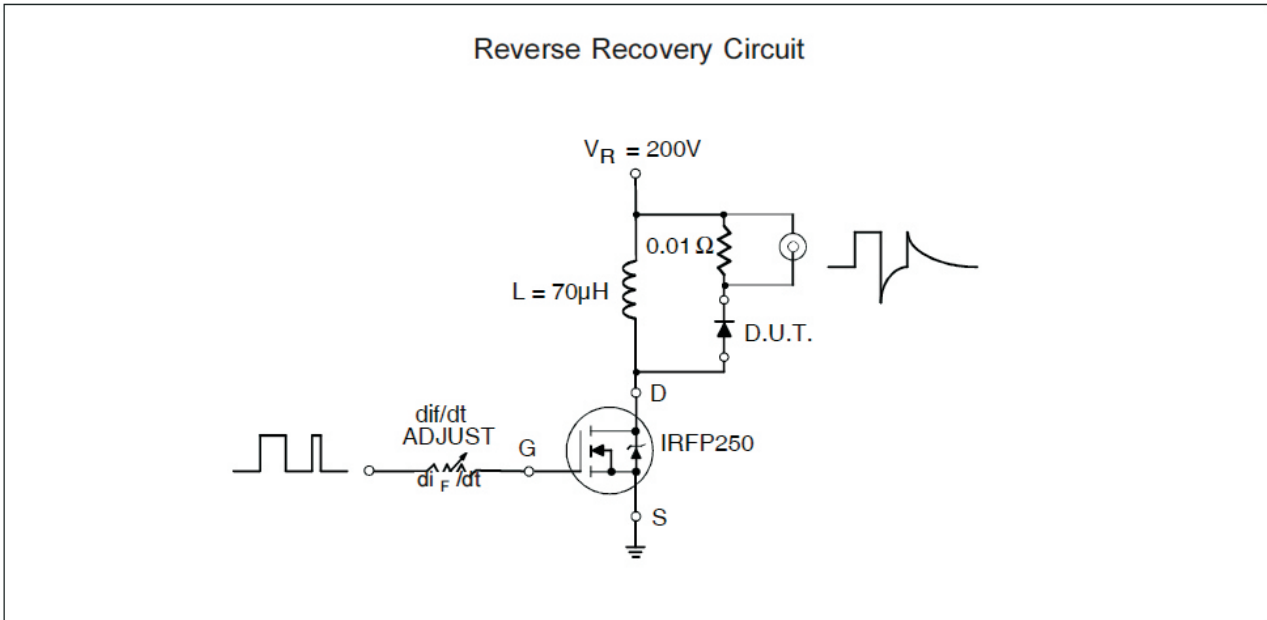
Device code



- 1 - Current rating (60 = 60A)
- 2 - Single Diode
- 3 - TO-247AC (Modified) or TO-247AB
- 4 - Ultrafast Recovery
- 5 - Voltage Rating (12 = 1200 V)

E = 2 pins  
 A = 3 pins

Fig.9 Reverse recovery parameter test circuit



- (3) Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;  
 $Pd = \text{Forward Power Loss} = I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$  (see Fig. 6);  
 $Pd_{REV} = \text{Inverse Power Loss} = V_{R1} \times I_R (1 - D)$ ;  $I_R @ V_{R1} = 80\% \text{ rated } V_R$

Fig.10 Reverse recovery waveform and definitions

